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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	516096
Number of I/O	341
Number of Gates	3000000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	484-BGA
Supplier Device Package	484-FPBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/m1a3pe3000-1fg484

I/Os Per Package¹

ProASIC3E Devices	A3PE600		A3PE1500 ³		A3PE3000 ³	
Cortex-M1 Devices ²			M1A3PE1500		M1A3PE3000	
Package	I/O Types					
	Single-Ended I/O ¹	Differential I/O Pairs	Single-Ended I/O ¹	Differential I/O Pairs	Single-Ended I/O ¹	Differential I/O Pairs
PQ208	147	65	147	65	147	65
FG256	165	79	–	–	–	–
FG324	–	–	–	–	221	110
FG484	270	135	280	139	341	168
FG676	–	–	444	222	–	–
FG896	–	–	–	–	620	310

Notes:

- When considering migrating your design to a lower- or higher-density device, refer to the [ProASIC3E FPGA Fabric User's Guide](#) to ensure compliance with design and board migration requirements.
- Each used differential I/O pair reduces the number of single-ended I/Os available by two.
- For A3PE1500 and A3PE3000 devices, the usage of certain I/O standards is limited as follows:
 - SSTL3(I) and (II): up to 40 I/Os per north or south bank
 - LVPECL / GTL+ 3.3 V / GTL 3.3 V: up to 48 I/Os per north or south bank
 - SSTL2(I) and (II) / GTL+ 2.5 V / GTL 2.5 V: up to 72 I/Os per north or south bank
- FG256 and FG484 are footprint-compatible packages.
- When using voltage-referenced I/O standards, one I/O pin should be assigned as a voltage-referenced pin (VREF) per minibank (group of I/Os).
- "G" indicates RoHS-compliant packages. Refer to the ["ProASIC3E Ordering Information"](#) on page III for the location of the "G" in the part number.

Table 1-2 • ProASIC3E FPGAs Package Sizes Dimensions

Package	PQ208	FG256	FG324	FG484	FG676	FG896
Length × Width (mm\mm)	28 × 28	17 × 17	19 × 19	23 × 23	27 × 27	31 × 31
Nominal Area (mm ²)	784	289	361	529	729	961
Pitch (mm)	0.5	1.0	1.0	1.0	1.0	1.0
Height (mm)	3.40	1.60	1.63	2.23	2.23	2.23

ProASIC3E Device Status

ProASIC3E Devices	Status	M1 ProASIC3E Devices	Status
A3PE600	Production		
A3PE1500	Production	M1A3PE1500	Production
A3PE3000	Production	M1A3PE3000	Production

1 – ProASIC3E Device Family Overview

General Description

ProASIC3E, the third-generation family of Microsemi flash FPGAs, offers performance, density, and features beyond those of the ProASIC^{PLUS}® family. Nonvolatile flash technology gives ProASIC3E devices the advantage of being a secure, low power, single-chip solution that is Instant On. ProASIC3E is reprogrammable and offers time-to-market benefits at an ASIC-level unit cost. These features enable designers to create high-density systems using existing ASIC or FPGA design flows and tools.

ProASIC3E devices offer 1 kbit of on-chip, programmable, nonvolatile FlashROM storage as well as clock conditioning circuitry based on six integrated phase-locked loops (PLLs). ProASIC3E devices have up to three million system gates, supported with up to 504 kbits of true dual-port SRAM and up to 620 user I/Os.

Several ProASIC3E devices support the Cortex-M1 soft IP cores, and the ARM-Enabled devices have Microsemi ordering numbers that begin with M1A3PE.

Flash Advantages

Reduced Cost of Ownership

Advantages to the designer extend beyond low unit cost, performance, and ease of use. Unlike SRAM-based FPGAs, flash-based ProASIC3E devices allow all functionality to be Instant On; no external boot PROM is required. On-board security mechanisms prevent access to all the programming information and enable secure remote updates of the FPGA logic. Designers can perform secure remote in-system reprogramming to support future design iterations and field upgrades with confidence that valuable intellectual property (IP) cannot be compromised or copied. Secure ISP can be performed using the industry-standard AES algorithm. The ProASIC3E family device architecture mitigates the need for ASIC migration at higher user volumes. This makes the ProASIC3E family a cost-effective ASIC replacement solution, especially for applications in the consumer, networking/ communications, computing, and avionics markets.

Security

The nonvolatile, flash-based ProASIC3E devices do not require a boot PROM, so there is no vulnerable external bitstream that can be easily copied. ProASIC3E devices incorporate FlashLock, which provides a unique combination of reprogrammability and design security without external overhead, advantages that only an FPGA with nonvolatile flash programming can offer.

ProASIC3E devices utilize a 128-bit flash-based lock and a separate AES key to provide the highest level of protection in the FPGA industry for programmed intellectual property and configuration data. In addition, all FlashROM data in ProASIC3E devices can be encrypted prior to loading, using the industry-leading AES-128 (FIPS192) bit block cipher encryption standard. The AES standard was adopted by the National Institute of Standards and Technology (NIST) in 2000 and replaces the 1977 DES standard. ProASIC3E devices have a built-in AES decryption engine and a flash-based AES key that make them the most comprehensive programmable logic device security solution available today. ProASIC3E devices with AES-based security provide a high level of protection for secure, remote field updates over public networks such as the Internet, and ensure that valuable IP remains out of the hands of system overbuilders, system cloners, and IP thieves.

Security, built into the FPGA fabric, is an inherent component of the ProASIC3E family. The flash cells are located beneath seven metal layers, and many device design and layout techniques have been used to make invasive attacks extremely difficult. The ProASIC3E family, with FlashLock and AES security, is unique in being highly resistant to both invasive and noninvasive attacks. Your valuable IP is protected with industry-standard security, making remote ISP possible. A ProASIC3E device provides the best available security for programmable logic designs.

Overview of I/O Performance

Summary of I/O DC Input and Output Levels – Default I/O Software Settings

Table 2-13 • Summary of Maximum and Minimum DC Input and Output Levels
Applicable to Commercial and Industrial Conditions

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option ¹	Slew Rate	VIL		VIH		VOL	VOH	IOL ³	IOH ³
				Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA
3.3 V LVTTTL / 3.3 V LVCMOS	12 mA	12 mA	High	–0.3	0.8	2	3.6	0.4	2.4	12	12
3.3 V LVCMOS Wide Range	100 μ A	12 mA	High	–0.3	0.8	2	3.6	0.2	VCCI – 0.2	0.1	0.1
2.5 V LVCMOS	12 mA	12 mA	High	–0.3	0.7	1.7	3.6	0.7	1.7	12	12
1.8 V LVCMOS	12 mA	12 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	12	12
1.5 V LVCMOS	12 mA	12 mA	High	–0.3	0.30 * VCCI	0.7 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	12	12
3.3 V PCI	Per PCI Specification										
3.3 V PCI-X	Per PCI-X Specification										
3.3 V GTL	20 mA ²	20 mA ²	High	–0.3	VREF – 0.05	VREF + 0.05	3.6	0.4	–	20	20
2.5 V GTL	20 mA ²	20 mA ²	High	–0.3	VREF – 0.05	VREF + 0.05	3.6	0.4	–	20	20
3.3 V GTL+	35 mA	35 mA	High	–0.3	VREF – 0.1	VREF + 0.1	3.6	0.6	–	35	35
2.5 V GTL+	33 mA	33 mA	High	–0.3	VREF – 0.1	VREF + 0.1	3.6	0.6	–	33	33
HSTL (I)	8 mA	8 mA	High	–0.3	VREF – 0.1	VREF + 0.1	3.6	0.4	VCCI – 0.4	8	8
HSTL (II)	15 mA ²	15 mA ²	High	–0.3	VREF – 0.1	VREF + 0.1	3.6	0.4	VCCI – 0.4	15	15
SSTL2 (I)	15 mA	15 mA	High	–0.3	VREF – 0.2	VREF + 0.2	3.6	0.54	VCCI – 0.62	15	15
SSTL2 (II)	18 mA	18 mA	High	–0.3	VREF – 0.2	VREF + 0.2	3.6	0.35	VCCI – 0.43	18	18
SSTL3 (I)	14 mA	14 mA	High	–0.3	VREF – 0.2	VREF + 0.2	3.6	0.7	VCCI – 1.1	14	14
SSTL3 (II)	21 mA	21 mA	High	–0.3	VREF – 0.2	VREF + 0.2	3.6	0.5	VCCI – 0.9	21	21

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100 \mu$ A. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. Output drive strength is below JEDEC specification.
3. Currents are measured at 85°C junction temperature.
4. Output Slew Rates can be extracted from [IBIS Models](http://www.microsemi.com/index.php?option=com_content&id=1671&lang=en&view=article), located at http://www.microsemi.com/index.php?option=com_content&id=1671&lang=en&view=article.

Table 2-36 • 2.5 V LVCMOS Low Slew
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.66	12.00	0.04	1.51	1.66	0.43	12.23	11.61	2.72	2.20	14.46	13.85	ns
	–1	0.56	10.21	0.04	1.29	1.41	0.36	10.40	9.88	2.31	1.87	12.30	11.78	ns
	–2	0.49	8.96	0.03	1.13	1.24	0.32	9.13	8.67	2.03	1.64	10.80	10.34	ns
8 mA	Std.	0.66	8.73	0.04	1.51	1.66	0.43	8.89	8.01	3.10	2.93	11.13	10.25	ns
	–1	0.56	7.43	0.04	1.29	1.41	0.36	7.57	6.82	2.64	2.49	9.47	8.72	ns
	–2	0.49	6.52	0.03	1.13	1.24	0.32	6.64	5.98	2.32	2.19	8.31	7.65	ns
12 mA	Std.	0.66	6.77	0.04	1.51	1.66	0.43	6.90	6.11	3.37	3.39	9.14	8.34	ns
	–1	0.56	5.76	0.04	1.29	1.41	0.36	5.87	5.20	2.86	2.89	7.77	7.10	ns
	–2	0.49	5.06	0.03	1.13	1.24	0.32	5.15	4.56	2.51	2.53	6.82	6.23	ns
16 mA	Std.	0.66	6.31	0.04	1.51	1.66	0.43	6.42	5.73	3.42	3.52	8.66	7.96	ns
	–1	0.56	5.37	0.04	1.29	1.41	0.36	5.46	4.87	2.91	3.00	7.37	6.77	ns
	–2	0.49	4.71	0.03	1.13	1.24	0.32	4.80	4.28	2.56	2.63	6.47	5.95	ns
24 mA	Std.	0.66	5.93	0.04	1.51	1.66	0.43	6.04	5.70	3.49	4.00	8.28	7.94	ns
	–1	0.56	5.05	0.04	1.29	1.41	0.36	5.14	4.85	2.97	3.40	7.04	6.75	ns
	–2	0.49	4.43	0.03	1.13	1.24	0.32	4.51	4.26	2.61	2.99	6.18	5.93	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-5](#) for derating values.

Voltage-Referenced I/O Characteristics

3.3 V GTL

Gunning Transceiver Logic is a high-speed bus standard (JESD8-3). It provides a differential amplifier input buffer and an open-drain output buffer. The VCCI pin should be connected to 3.3 V.

Table 2-48 • Minimum and Maximum DC Input and Output Levels

3.3 V GTL	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ¹	Max. mA ¹	μA ²	μA ²
20 mA ³	−0.3	VREF − 0.05	VREF + 0.05	3.6	0.4	−	20	20	181	268	10	10

Notes:

1. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
2. Currents are measured at 85°C junction temperature.
3. Output drive strength is below JEDEC specification.

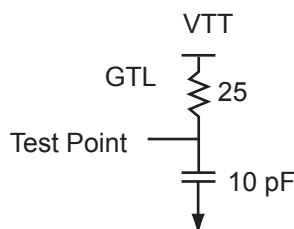


Figure 2-12 • AC Loading

Table 2-49 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C _{LOAD} (pF)
VREF − 0.05	VREF + 0.05	0.8	0.8	1.2	10

Note: *Measuring point = V_{trip}. See Table 2-15 on page 2-18 for a complete table of trip points.

Timing Characteristics

Table 2-50 • 3.3 V GTL

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCI = 3.0 V VREF = 0.8 V

Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
Std.	0.60	2.08	0.04	2.93	0.43	2.04	2.08			4.27	4.31	ns
−1	0.51	1.77	0.04	2.50	0.36	1.73	1.77			3.63	3.67	ns
−2	0.45	1.55	0.03	2.19	0.32	1.52	1.55			3.19	3.22	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

LVPECL

Low-Voltage Positive Emitter-Coupled Logic (LVPECL) is another differential I/O standard. It requires that one data bit be carried through two signal lines. Like LVDS, two pins are needed. It also requires external resistor termination.

The full implementation of the LVDS transmitter and receiver is shown in an example in [Figure 2-24](#). The building blocks of the LVPECL transmitter-receiver are one transmitter macro, one receiver macro, three board resistors at the transmitter end, and one resistor at the receiver end. The values for the three driver resistors are different from those used in the LVDS implementation because the output standard specifications are different.

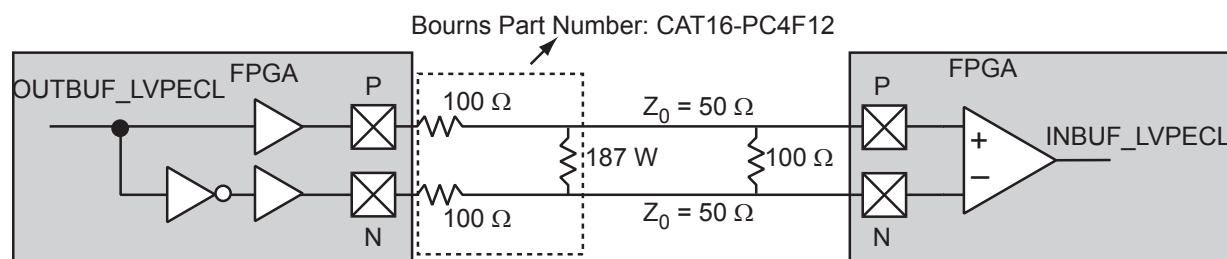


Figure 2-24 • LVPECL Circuit Diagram and Board-Level Implementation

Table 2-81 • Minimum and Maximum DC Input and Output Levels

DC Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Units
VCCI	Supply Voltage	3.0		3.3		3.6		V
VOL	Output Low Voltage	0.96	1.27	1.06	1.43	1.30	1.57	V
VOH	Output High Voltage	1.8	2.11	1.92	2.28	2.13	2.41	V
VIL, VIH	Input Low, Input High Voltages	0	3.6	0	3.6	0	3.6	V
VODIFF	Differential Output Voltage	0.625	0.97	0.625	0.97	0.625	0.97	V
VOCM	Output Common-Mode Voltage	1.762	1.98	1.762	1.98	1.762	1.98	V
VICM	Input Common-Mode Voltage	1.01	2.57	1.01	2.57	1.01	2.57	V
VIDIFF	Input Differential Voltage	300		300		300		mV

Table 2-82 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)
1.64	1.94	Cross point	—

Note: *Measuring point = V_{trip} . See [Table 2-15 on page 2-18](#) for a complete table of trip points.

Timing Characteristics

Table 2-83 • LVPECL

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	Units
Std.	0.66	1.83	0.04	1.63	ns
–1	0.56	1.55	0.04	1.39	ns
–2	0.49	1.36	0.03	1.22	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-5](#) for derating values.

I/O Register Specifications

Fully Registered I/O Buffers with Synchronous Enable and Asynchronous Preset

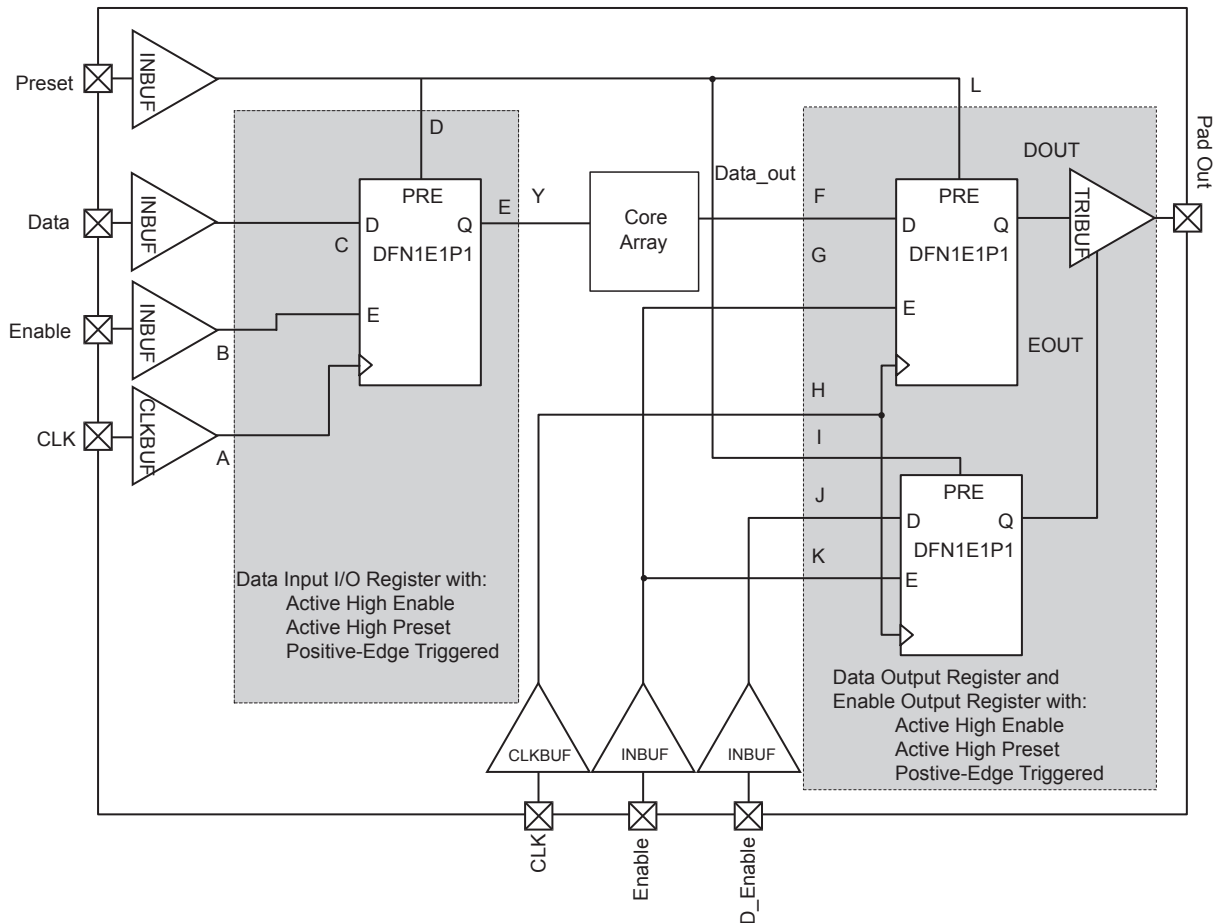


Figure 2-25 • Timing Model of Registered I/O Buffers with Synchronous Enable and Asynchronous Preset

Table 2-84 • Parameter Definition and Measuring Nodes

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	H, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	F, H
t_{OHD}	Data Hold Time for the Output Data Register	F, H
t_{OSUE}	Enable Setup Time for the Output Data Register	G, H
t_{OHE}	Enable Hold Time for the Output Data Register	G, H
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	L, DOUT
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	L, H
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	L, H
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	H, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	J, H
t_{OEHD}	Data Hold Time for the Output Enable Register	J, H
t_{OESUE}	Enable Setup Time for the Output Enable Register	K, H
t_{OEHE}	Enable Hold Time for the Output Enable Register	K, H
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	I, EOUT
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	I, H
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	I, H
t_{ICLKQ}	Clock-to-Q of the Input Data Register	A, E
t_{ISUD}	Data Setup Time for the Input Data Register	C, A
t_{IHD}	Data Hold Time for the Input Data Register	C, A
t_{ISUE}	Enable Setup Time for the Input Data Register	B, A
t_{IHE}	Enable Hold Time for the Input Data Register	B, A
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	D, E
$t_{IREMPRE}$	Asynchronous Preset Removal Time for the Input Data Register	D, A
$t_{IRECPRE}$	Asynchronous Preset Recovery Time for the Input Data Register	D, A

Note: *See Figure 2-25 on page 2-53 for more information.

Timing Waveforms

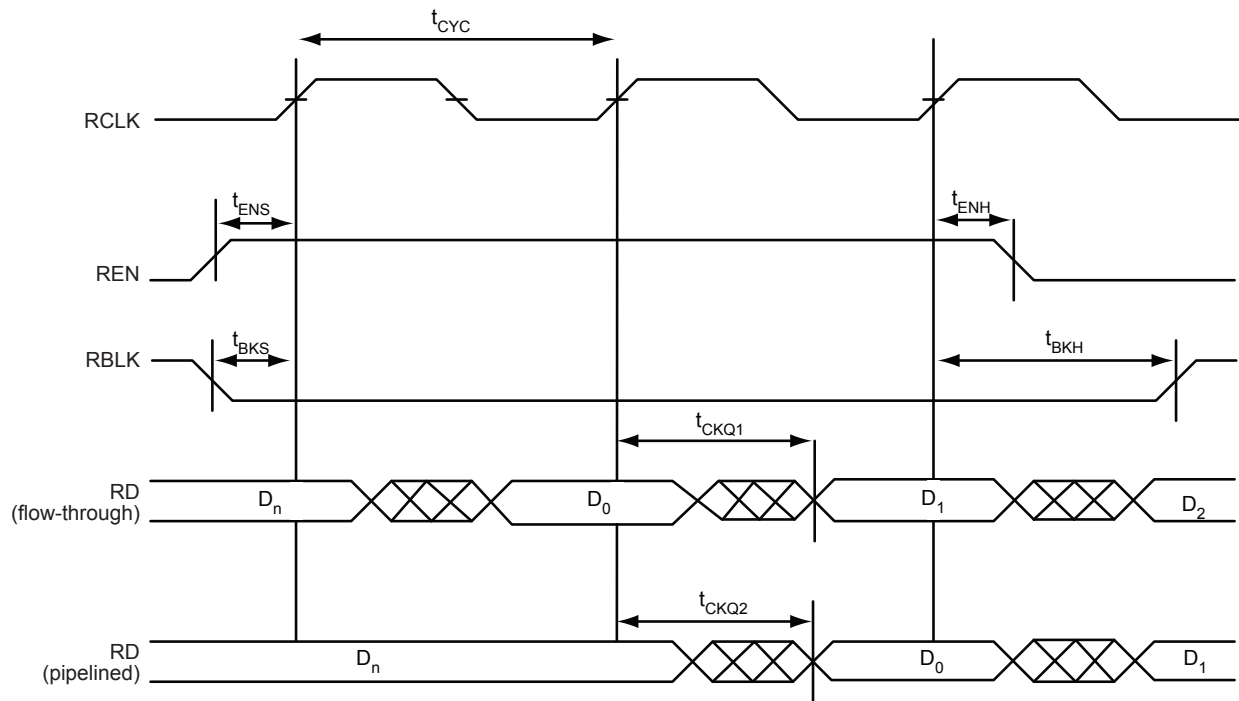


Figure 2-47 • FIFO Read

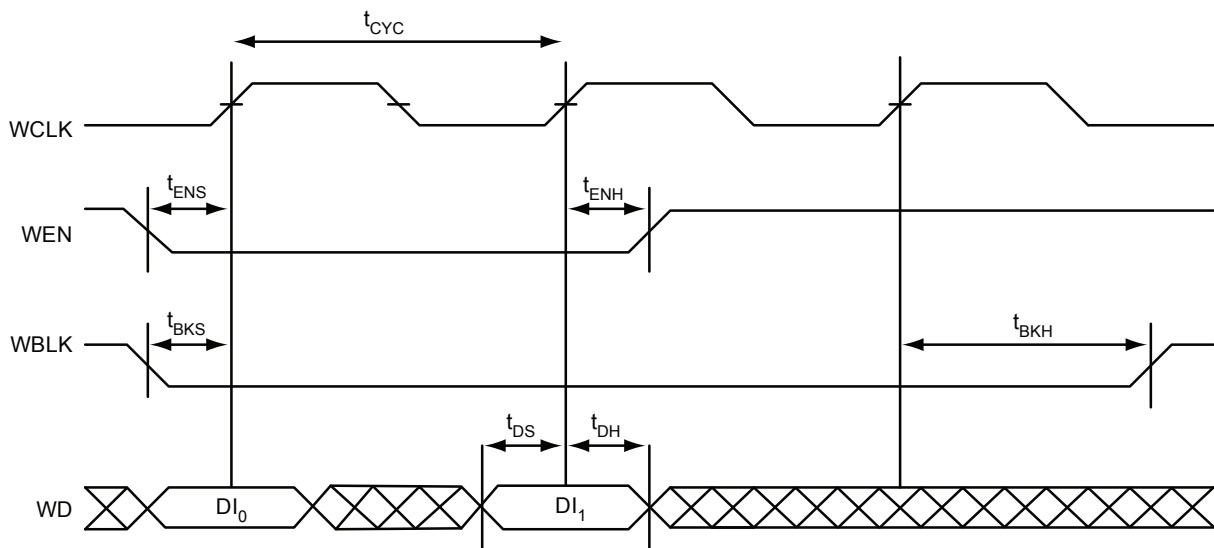


Figure 2-48 • FIFO Write

Special Function Pins

NC

No Connect

This pin is not connected to circuitry within the device. These pins can be driven to any voltage or can be left floating with no effect on the operation of the device.

DC

Do Not Connect

This pin should not be connected to any signals on the PCB. These pins should be left unconnected.

Packaging

Semiconductor technology is constantly shrinking in size while growing in capability and functional integration. To enable next-generation silicon technologies, semiconductor packages have also evolved to provide improved performance and flexibility.

Microsemi consistently delivers packages that provide the necessary mechanical and environmental protection to ensure consistent reliability and performance. Microsemi IC packaging technology efficiently supports high-density FPGAs with large-pin-count Ball Grid Arrays (BGAs), but is also flexible enough to accommodate stringent form factor requirements for Chip Scale Packaging (CSP). In addition, Microsemi offers a variety of packages designed to meet your most demanding application and economic requirements for today's embedded and mobile systems.

Related Documents

User's Guides

ProASIC3E FPGA Fabric User's Guide

http://www.microsemi.com/document-portal/doc_download/130883-proasic3e-fpga-fabric-user-s-guide

Packaging

The following documents provide packaging information and device selection for low power flash devices.

Product Catalog

http://www.microsemi.com/soc/documents/ProdCat_PIB.pdf

Lists devices currently recommended for new designs and the packages available for each member of the family. Use this document or the datasheet tables to determine the best package for your design, and which package drawing to use.

Package Mechanical Drawings

http://www.microsemi.com/document-portal/doc_download/131095-package-mechanical-drawings

This document contains the package mechanical drawings for all packages currently or previously supplied by Microsemi. Use the bookmarks to navigate to the package mechanical drawings.

Additional packaging materials: <http://www.microsemi.com/products/fpga-soc/solutions>.

PQ208	
Pin Number	A3PE600 Function
1	GND
2	GNDQ
3	VMV7
4	GAB2/IO133PSB7V1
5	GAA2/IO134PDB7V1
6	IO134NDB7V1
7	GAC2/IO132PDB7V1
8	IO132NDB7V1
9	IO130PDB7V1
10	IO130NDB7V1
11	IO127PDB7V1
12	IO127NDB7V1
13	IO126PDB7V0
14	IO126NDB7V0
15	IO124PSB7V0
16	VCC
17	GND
18	VCCIB7
19	IO122PPB7V0
20	IO121PSB7V0
21	IO122NPB7V0
22	GFC1/IO120PSB7V0
23	GFB1/IO119PDB7V0
24	GFB0/IO119NDB7V0
25	VCOMPLF
26	GFA0/IO118NPB6V1
27	VCCPLF
28	GFA1/IO118PPB6V1
29	GND
30	GFA2/IO117PDB6V1
31	IO117NDB6V1
32	GFB2/IO116PPB6V1
33	GFC2/IO115PPB6V1
34	IO116NPB6V1
35	IO115NPB6V1
36	VCC

PQ208	
Pin Number	A3PE600 Function
37	IO112PDB6V1
38	IO112NDB6V1
39	IO108PSB6V0
40	VCCIB6
41	GND
42	IO106PDB6V0
43	IO106NDB6V0
44	GEC1/IO104PDB6V0
45	GEC0/IO104NDB6V0
46	GEB1/IO103PPB6V0
47	GEA1/IO102PPB6V0
48	GEB0/IO103NPB6V0
49	GEA0/IO102NPB6V0
50	VMV6
51	GNDQ
52	GND
53	VMV5
54	GNDQ
55	IO101NDB5V2
56	GEA2/IO101PDB5V2
57	IO100NDB5V2
58	GEB2/IO100PDB5V2
59	IO99NDB5V2
60	GEC2/IO99PDB5V2
61	IO98PSB5V2
62	VCCIB5
63	IO96PSB5V2
64	IO94NDB5V1
65	GND
66	IO94PDB5V1
67	IO92NDB5V1
68	IO92PDB5V1
69	IO88NDB5V0
70	IO88PDB5V0
71	VCC

PQ208	
Pin Number	A3PE600 Function
72	VCCIB5
73	IO85NPB5V0
74	IO84NPB5V0
75	IO85PPB5V0
76	IO84PPB5V0
77	IO83NPB5V0
78	IO82NPB5V0
79	IO83PPB5V0
80	IO82PPB5V0
81	GND
82	IO80NDB4V1
83	IO80PDB4V1
84	IO79NPB4V1
85	IO78NPB4V1
86	IO79PPB4V1
87	IO78PPB4V1
88	VCC
89	VCCIB4
90	IO76NDB4V1
91	IO76PDB4V1
92	IO72NDB4V0
93	IO72PDB4V0
94	IO70NDB4V0
95	GDC2/IO70PDB4V0
96	IO68NDB4V0
97	GND
98	GDA2/IO68PDB4V0
99	GDB2/IO69PSB4V0
100	GNDQ
101	TCK
102	TDI
103	TMS
104	VMV4
105	GND
106	VPUMP
107	GNDQ

PQ208	
Pin Number	A3PE600 Function
108	TDO
109	TRST
110	VJTAG
111	VMV3
112	GDA0/IO67NPB3V1
113	GDB0/IO66NPB3V1
114	GDA1/IO67PPB3V1
115	GDB1/IO66PPB3V1
116	GDC0/IO65NDB3V1
117	GDC1/IO65PDB3V1
118	IO62NDB3V1
119	IO62PDB3V1
120	IO58NDB3V0
121	IO58PDB3V0
122	GND
123	VCCIB3
124	GCC2/IO55PSB3V0
125	GCB2/IO54PSB3V0
126	NC
127	IO53NDB3V0
128	GCA2/IO53PDB3V0
129	GCA1/IO52PPB3V0
130	GND
131	VCCPLC
132	GCA0/IO52NPB3V0
133	VCOMPLC
134	GCB0/IO51NDB2V1
135	GCB1/IO51PDB2V1
136	GCC1/IO50PSB2V1
137	IO49NDB2V1
138	IO49PDB2V1
139	IO48PSB2V1
140	VCCIB2
141	GND
142	VCC
143	IO47NDB2V1

PQ208	
Pin Number	A3PE600 Function
144	IO47PDB2V1
145	IO44NDB2V1
146	IO44PDB2V1
147	IO43NDB2V0
148	IO43PDB2V0
149	IO40NDB2V0
150	IO40PDB2V0
151	GBC2/IO38PSB2V0
152	GBA2/IO36PSB2V0
153	GBB2/IO37PSB2V0
154	VMV2
155	GNDQ
156	GND
157	VMV1
158	GNDQ
159	GBA1/IO35PDB1V1
160	GBA0/IO35NDB1V1
161	GBB1/IO34PDB1V1
162	GND
163	GBB0/IO34NDB1V1
164	GBC1/IO33PDB1V1
165	GBC0/IO33NDB1V1
166	IO31PDB1V1
167	IO31NDB1V1
168	IO27PDB1V0
169	IO27NDB1V0
170	VCCIB1
171	VCC
172	IO23PPB1V0
173	IO22PSB1V0
174	IO23NPB1V0
175	IO21PDB1V0
176	IO21NDB1V0
177	IO19PPB0V2
178	GND
179	IO18PPB0V2

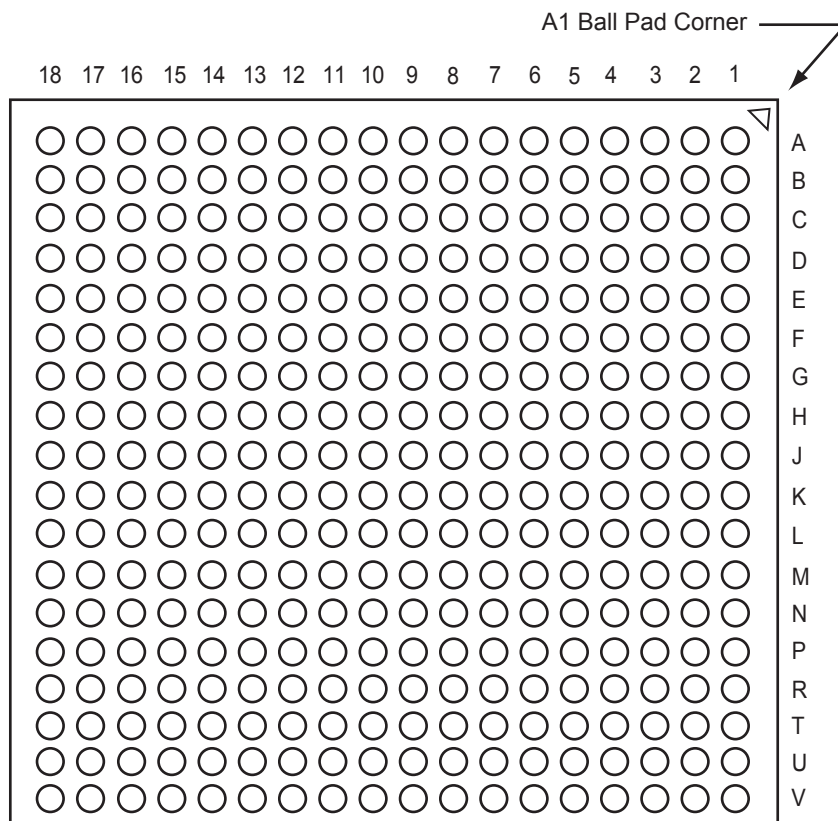
PQ208	
Pin Number	A3PE600 Function
180	IO19NPB0V2
181	IO18NPB0V2
182	IO17PPB0V2
183	IO16PPB0V2
184	IO17NPB0V2
185	IO16NPB0V2
186	VCCIB0
187	VCC
188	IO15PDB0V2
189	IO15NDB0V2
190	IO13PDB0V2
191	IO13NDB0V2
192	IO11PSB0V1
193	IO09PDB0V1
194	IO09NDB0V1
195	GND
196	IO07PDB0V1
197	IO07NDB0V1
198	IO05PDB0V0
199	IO05NDB0V0
200	VCCIB0
201	GAC1/IO02PDB0V0
202	GAC0/IO02NDB0V0
203	GAB1/IO01PDB0V0
204	GAB0/IO01NDB0V0
205	GAA1/IO00PDB0V0
206	GAA0/IO00NDB0V0
207	GNDQ
208	VMV0

PQ208	
Pin Number	A3PE1500 Function
1	GND
2	GNDQ
3	VMV7
4	GAB2/IO220PSB7V3
5	GAA2/IO221PDB7V3
6	IO221NDB7V3
7	GAC2/IO219PDB7V3
8	IO219NDB7V3
9	IO215PDB7V3
10	IO215NDB7V3
11	IO212PDB7V2
12	IO212NDB7V2
13	IO208PDB7V2
14	IO208NDB7V2
15	IO204PSB7V1
16	VCC
17	GND
18	VCCIB7
19	IO200PDB7V1
20	IO200NDB7V1
21	IO196PSB7V0
22	GFC1/IO192PSB7V0
23	GFB1/IO191PDB7V0
24	GFB0/IO191NDB7V0
25	VCOMPLF
26	GFA0/IO190NPB6V2
27	VCCPLF
28	GFA1/IO190PPB6V2
29	GND
30	GFA2/IO189PDB6V2
31	IO189NDB6V2
32	GFB2/IO188PPB6V2
33	GFC2/IO187PPB6V2
34	IO188NPB6V2
35	IO187NPB6V2
36	VCC

PQ208	
Pin Number	A3PE1500 Function
37	IO184PDB6V2
38	IO184NDB6V2
39	IO180PSB6V1
40	VCCIB6
41	GND
42	IO176PDB6V1
43	IO176NDB6V1
44	GEC1/IO169PDB6V0
45	GEC0/IO169NDB6V0
46	GEB1/IO168PPB6V0
47	GEA1/IO167PPB6V0
48	GEB0/IO168NPB6V0
49	GEA0/IO167NPB6V0
50	VMV6
51	GNDQ
52	GND
53	VMV5
54	GNDQ
55	IO166NDB5V3
56	GEA2/IO166PDB5V3
57	IO165NDB5V3
58	GEB2/IO165PDB5V3
59	IO164NDB5V3
60	GEC2/IO164PDB5V3
61	IO163PSB5V3
62	VCCIB5
63	IO161PSB5V3
64	IO157NDB5V2
65	GND
66	IO157PDB5V2
67	IO153NDB5V2
68	IO153PDB5V2
69	IO149NDB5V1
70	IO149PDB5V1
71	VCC
72	VCCIB5

PQ208	
Pin Number	A3PE1500 Function
73	IO145NDB5V1
74	IO145PDB5V1
75	IO143NDB5V1
76	IO143PDB5V1
77	IO137NDB5V0
78	IO137PDB5V0
79	IO135NDB5V0
80	IO135PDB5V0
81	GND
82	IO131NDB4V2
83	IO131PDB4V2
84	IO129NDB4V2
85	IO129PDB4V2
86	IO127NDB4V2
87	IO127PDB4V2
88	VCC
89	VCCIB4
90	IO121NDB4V1
91	IO121PDB4V1
92	IO119NDB4V1
93	IO119PDB4V1
94	IO113NDB4V0
95	GDC2/IO113PDB4V0
96	IO112NDB4V0
97	GND
98	GDB2/IO112PDB4V0
99	GDA2/IO111PSB4V0
100	GNDQ
101	TCK
102	TDI
103	TMS
104	VMV4
105	GND
106	VPUMP
107	GNDQ
108	TDO

FG324



Note: This is the bottom view of the package.

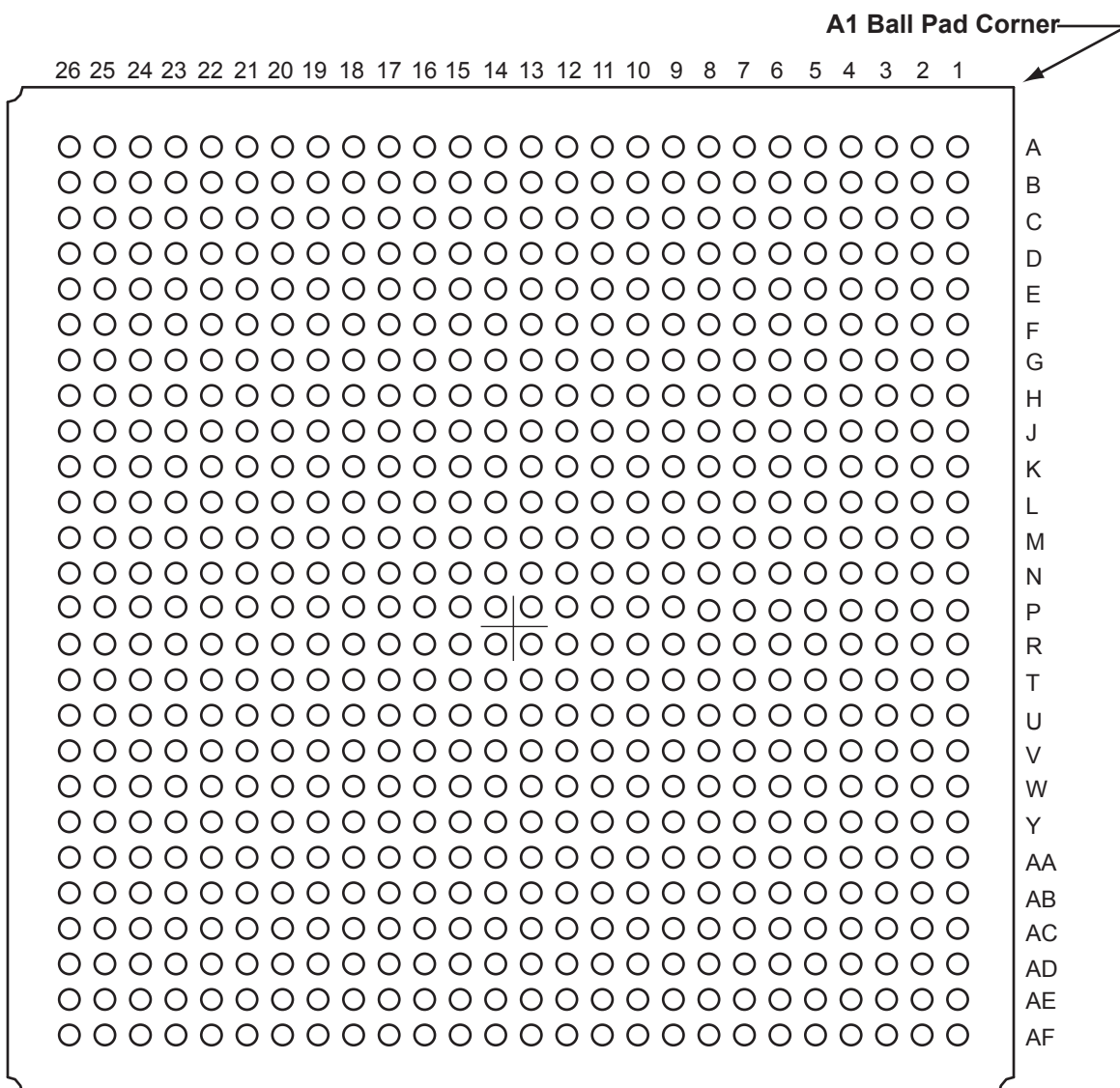
Note

For Package Manufacturing and Environmental information, visit the Resource Center at <http://www.microsemi.com/products/fpga-soc/solutions>.

FG484	
Pin Number	A3PE1500 Function
V15	IO112NDB4V0
V16	GDB2/IO112PDB4V0
V17	TDI
V18	GNDQ
V19	TDO
V20	GND
V21	NC
V22	IO105NDB3V2
W1	NC
W2	NC
W3	NC
W4	GND
W5	IO165NDB5V3
W6	GEB2/IO165PDB5V3
W7	IO164NDB5V3
W8	IO153NDB5V2
W9	IO153PDB5V2
W10	IO147NDB5V1
W11	IO133NDB4V2
W12	IO130NDB4V2
W13	IO130PDB4V2
W14	IO113NDB4V0
W15	GDC2/IO113PDB4V0
W16	IO111NDB4V0
W17	GDA2/IO111PDB4V0
W18	TMS
W19	GND
W20	NC
W21	NC
W22	NC
Y1	VCCIB6
Y2	NC
Y3	NC
Y4	IO161NDB5V3
Y5	GND
Y6	IO163NDB5V3

FG484	
Pin Number	A3PE1500 Function
Y7	IO163PDB5V3
Y8	VCC
Y9	VCC
Y10	IO147PDB5V1
Y11	IO133PDB4V2
Y12	IO131NPB4V2
Y13	NC
Y14	VCC
Y15	VCC
Y16	NC
Y17	NC
Y18	GND
Y19	NC
Y20	NC
Y21	NC
Y22	VCCIB3

FG676



Note: This is the bottom view of the package.

Note

For Package Manufacturing and Environmental information, visit the Resource Center at <http://www.microsemi.com/products/fpga-soc/solutions>.

FG676	
Pin Number	A3PE1500 Function
L17	GND
L18	VCC
L19	VCCIB2
L20	IO67PDB2V1
L21	IO67NDB2V1
L22	IO71PDB2V2
L23	IO71NDB2V2
L24	GNDQ
L25	IO82PDB2V3
L26	IO84NDB2V3
M1	IO198NPB7V0
M2	IO202PDB7V1
M3	IO202NDB7V1
M4	IO206NDB7V1
M5	IO206PDB7V1
M6	IO204NDB7V1
M7	IO204PDB7V1
M8	VCCIB7
M9	VCC
M10	GND
M11	GND
M12	GND
M13	GND
M14	GND
M15	GND
M16	GND
M17	GND
M18	VCC
M19	VCCIB2
M20	IO73NDB2V2
M21	IO73PDB2V2
M22	IO81PPB2V3
M23	IO77PDB2V2
M24	IO77NDB2V2
M25	IO82NDB2V3
M26	IO83PDB2V3

FG676	
Pin Number	A3PE1500 Function
N1	GFB0/IO191NPB7V0
N2	VCOMPLF
N3	GFB1/IO191PPB7V0
N4	IO196PDB7V0
N5	GFA0/IO190NDB6V2
N6	IO200PDB7V1
N7	IO200NDB7V1
N8	VCCIB7
N9	VCC
N10	GND
N11	GND
N12	GND
N13	GND
N14	GND
N15	GND
N16	GND
N17	GND
N18	VCC
N19	VCCIB2
N20	IO79PDB2V3
N21	IO79NDB2V3
N22	GCA2/IO88PPB3V0
N23	IO81NPB2V3
N24	GCA0/IO87NDB3V0
N25	GCB0/IO86NPB2V3
N26	IO83NDB2V3
P1	GFA2/IO189PDB6V2
P2	VCCPLF
P3	IO193PPB7V0
P4	IO196NDB7V0
P5	GFA1/IO190PDB6V2
P6	IO194PDB7V0
P7	IO194NDB7V0
P8	VCCIB6
P9	VCC
P10	GND

FG676	
Pin Number	A3PE1500 Function
P11	GND
P12	GND
P13	GND
P14	GND
P15	GND
P16	GND
P17	GND
P18	VCC
P19	VCCIB3
P20	GCC0/IO85NDB2V3
P21	GCC1/IO85PDB2V3
P22	GCB1/IO86PPB2V3
P23	IO88NPB3V0
P24	GCA1/IO87PDB3V0
P25	VCCPLC
P26	VCOMPLC
R1	IO189NDB6V2
R2	IO185PDB6V2
R3	IO187NPB6V2
R4	IO193NPB7V0
R5	GFC2/IO187PPB6V2
R6	GFC1/IO192PDB7V0
R7	GFC0/IO192NDB7V0
R8	VCCIB6
R9	VCC
R10	GND
R11	GND
R12	GND
R13	GND
R14	GND
R15	GND
R16	GND
R17	GND
R18	VCC
R19	VCCIB3
R20	NC

Revision	Changes	Page
Revision 10 (March 2012)	The "In-System Programming (ISP) and Security" section and "Security" section were revised to clarify that although no existing security measures can give an absolute guarantee, Microsemi FPGAs implement the best security available in the industry (SAR 34669).	I, 1-1
	The Y security option and Licensed DPA Logo were added to the "ProASIC3E Ordering Information" section. The trademarked Licensed DPA Logo identifies that a product is covered by a DPA counter-measures license from Cryptography Research (SAR 34727).	III
	The following sentence was removed from the "Advanced Architecture" section: "In addition, extensive on-chip programming circuitry allows for rapid, single-voltage (3.3 V) programming of IGLOOe devices via an IEEE 1532 JTAG interface" (SAR 34689).	1-3
	The "Specifying I/O States During Programming" section is new (SAR 34699).	1-6
	VCCPLL in Table 2-2 • Recommended Operating Conditions ¹ was corrected from "1.4 to 1.6 V" to "1.425 to 1.575 V" (SAR 33851). The T _J symbol was added to the table and notes regarding T _A and T _J were removed. The second of two parameters in the VCCI and VMV row, called "3.3 V DC supply voltage," was corrected to "3.0 V DC supply voltage" (SAR 37227).	2-2
	The reference to guidelines for global spines and VersaTile rows, given in the "Global Clock Contribution—P _{CLOCK} " section, was corrected to the "Spine Architecture" section of the Global Resources chapter in the <i>ProASIC3E FPGA Fabric User's Guide</i> (SAR 34735).	2-9
	t _{DOUT} was corrected to t _{DIN} in Figure 2-3 • Input Buffer Timing Model and Delays (example) (SAR 37109).	2-13
	The typo related to the values for 3.3 V LVCMOS Wide Range in Table 2-17 • Summary of I/O Timing Characteristics—Software Default Settings was corrected (SAR 37227).	2-19
	The notes regarding drive strength in the "Summary of I/O Timing Characteristics – Default I/O Software Settings" section and "3.3 V LVCMOS Wide Range" section and tables were revised for clarification. They now state that the minimum drive strength for the default software configuration when run in wide range is ±100 µA. The drive strength displayed in software is supported in normal range only. For a detailed I/V curve, refer to the IBIS models (SAR 34763).	2-18, 2-27

Revision	Changes	Page
Advance v0.5 (continued)	The "RESET" section was updated.	2-25
	The "RESET" section was updated.	2-27
	The "Introduction" of the "Introduction" section was updated.	2-28
	PCI-X 3.3 V was added to the Compatible Standards for 3.3 V in Table 2-11 • VCCI Voltages and Compatible Standards	2-29
	Table 2-35 • ProASIC3E I/O Features was updated.	2-54
	The "Double Data Rate (DDR) Support" section was updated to include information concerning implementation of the feature.	2-32
	The "Electrostatic Discharge (ESD) Protection" section was updated to include testing information.	2-35
	Level 3 and 4 descriptions were updated in Table 2-43 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in ProASIC3 Devices.	2-64
	The notes in Table 2-45 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in ProASIC3E Devices were updated.	2-64
	The "Simultaneous Switching Outputs (SSOs) and Printed Circuit Board Layout" section is new.	2-41
	A footnote was added to Table 2-37 • Maximum I/O Frequency for Single-Ended and Differential I/Os in All Banks in ProASIC3E Devices (maximum drive strength and high slew selected).	2-55
	Table 2-48 • ProASIC3E I/O Attributes vs. I/O Standard Applications	2-81
	Table 2-55 • ProASIC3 I/O Standards—SLEW and Output Drive (OUT_DRIVE) Settings	2-85
	The "x" was updated in the "Pin Descriptions" section.	2-50
	The "VCC Core Supply Voltage" pin description was updated.	2-50
	The "VMVx I/O Supply Voltage (quiet)" pin description was updated to include information concerning leaving the pin unconnected.	2-50
	EXTFB was removed from Figure 2-24 • ProASIC3E CCC Options.	2-24
	The CCC Output Peak-to-Peak Period Jitter F_{CCC_OUT} was updated in Table 2-13 • ProASIC3E CCC/PLL Specification.	2-30
	EXTFB was removed from Figure 2-27 • CCC/PLL Macro.	2-28
	The LVPECL specification in Table 2-45 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in ProASIC3E Devices was updated.	2-64
	Table 2-15 • Levels of Hot-Swap Support was updated.	2-34
	The "Cold-Sparing Support" section was updated.	2-34
	"Electrostatic Discharge (ESD) Protection" section was updated.	2-35
	The VJTAG and I/O pin descriptions were updated in the "Pin Descriptions" section.	2-50
	The "VJTAG JTAG Supply Voltage" pin description was updated.	2-50
	The "VPUMP Programming Supply Voltage" pin description was updated to include information on what happens when the pin is tied to ground.	2-50

Datasheet Categories

Categories

In order to provide the latest information to designers, some datasheet parameters are published before data has been fully characterized from silicon devices. The data provided for a given device, as highlighted in the ["ProASIC3E Device Status" table on page II](#), is designated as either "Product Brief," "Advance," "Preliminary," or "Production." The definitions of these categories are as follows:

Product Brief

The product brief is a summarized version of a datasheet (advance or production) and contains general product information. This document gives an overview of specific device and family information.

Advance

This version contains initial estimated information based on simulation, other products, devices, or speed grades. This information can be used as estimates, but not for production. This label only applies to the DC and Switching Characteristics chapter of the datasheet and will only be used when the data has not been fully characterized.

Preliminary

The datasheet contains information based on simulation and/or initial characterization. The information is believed to be correct, but changes are possible.

Production

This version contains information that is considered to be final.

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